

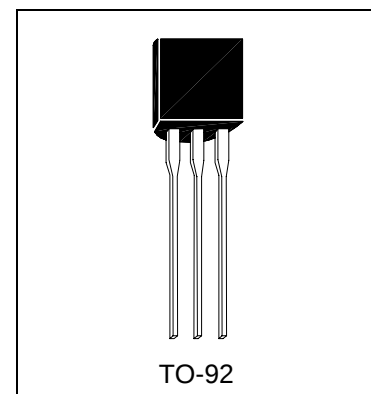


HSB562

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The HSB562 is designed for general purpose low frequency power amplifier applications.



Absolute Maximum Ratings

- Maximum Temperatures
Storage Temperature -55 ~ +150 °C
Junction Temperature +150 °C Maximum
- Maximum Power Dissipation
Total Power Dissipation ($T_A=25^{\circ}\text{C}$) 900 mW
- Maximum Voltages and Currents ($T_A=25^{\circ}\text{C}$)
 V_{CBO} Collector to Base Voltage -25 V
 V_{CEO} Collector to Emitter Voltage -20 V
 V_{EBO} Emitter to Base Voltage -5 V
 I_C Collector Current -1 A

Electrical Characteristics ($T_A=25^{\circ}\text{C}$)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	-25	-	-	V	$I_C=-10\mu\text{A}$, $I_E=0$
BV_{CEO}	-20	-	-	V	$I_C=-1\text{mA}$, $I_B=0$
BV_{EBO}	-5	-	-	V	$I_E=-10\mu\text{A}$, $I_C=0$
I_{CBO}	-	-	-1	μA	$V_{CB}=-20\text{V}$, $I_E=0$
$*V_{CE(sat)}$	-	-	-500	mV	$I_C=-800\text{mA}$, $I_B=-80\text{mA}$
$V_{BE(on)}$	-	-	-1	V	$I_C=-500\text{mA}$, $V_{CE}=-2\text{V}$
$*h_{FE}$	85	-	240		$V_{CE}=-2\text{V}$, $I_C=-500\text{mA}$
f_T	-	350	-	MHz	$V_{CE}=-2\text{V}$, $I_C=-500\text{mA}$
Cob	-	38	-	pF	$V_{CB}=-10\text{V}$, $f=1\text{MHz}$

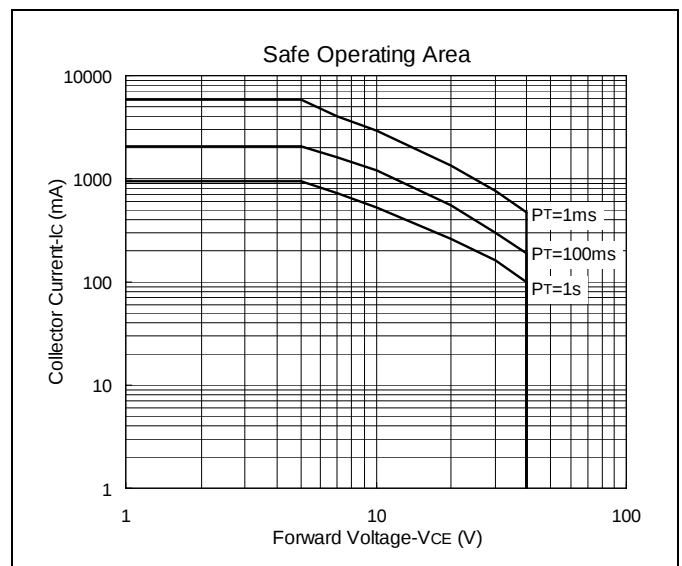
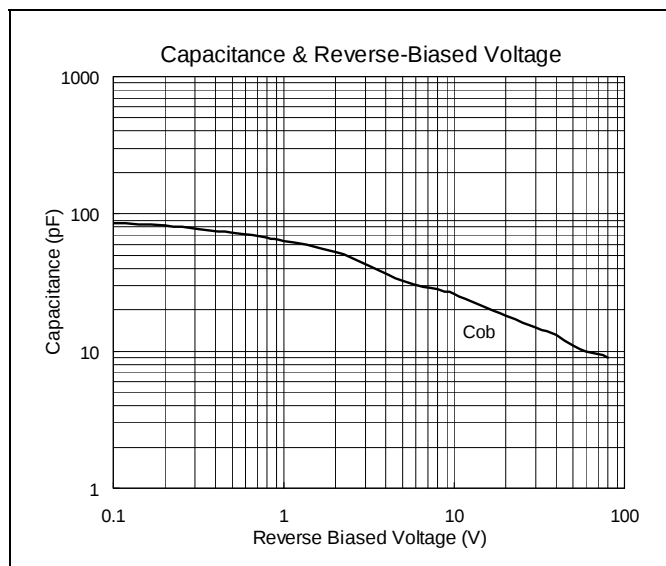
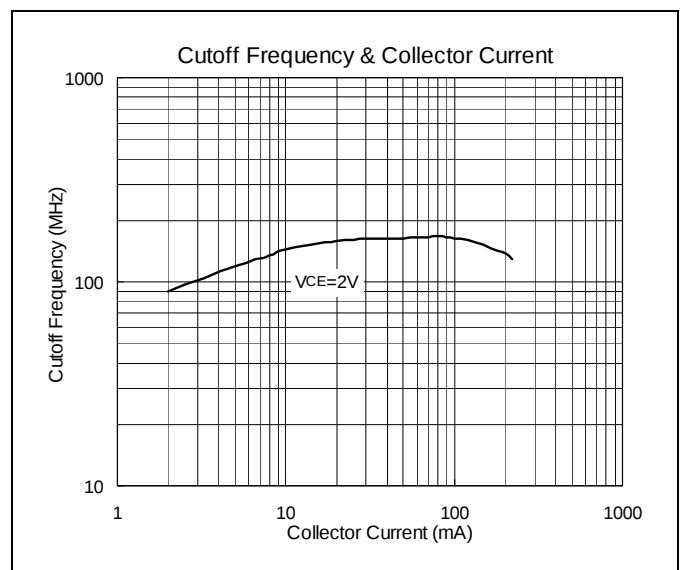
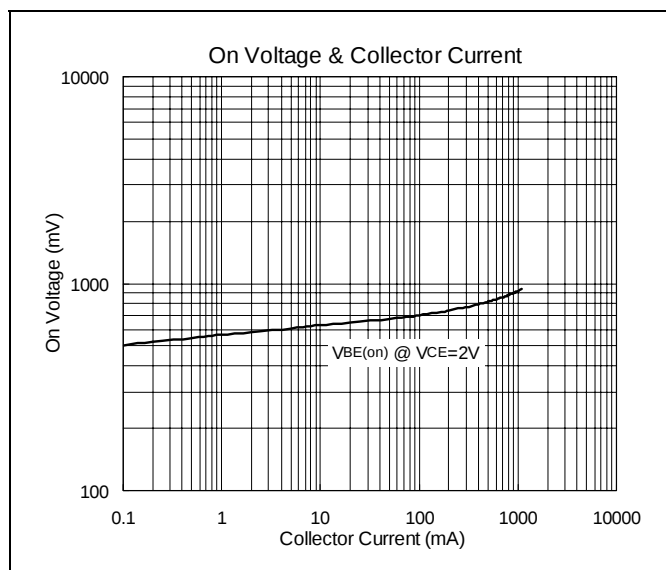
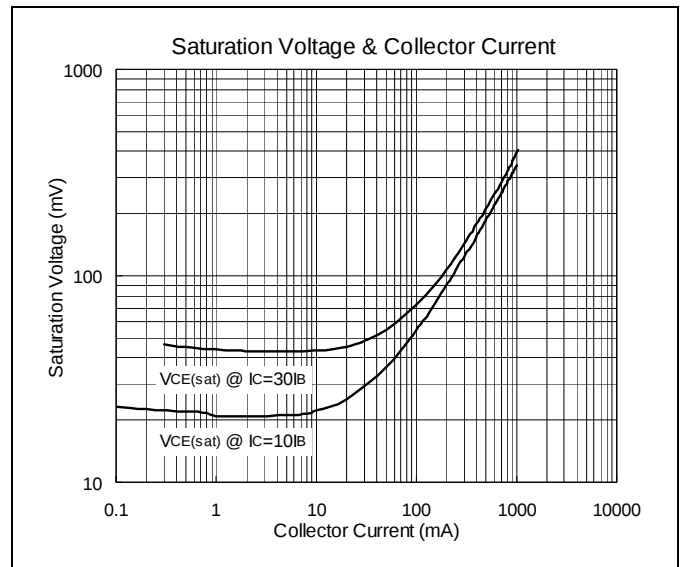
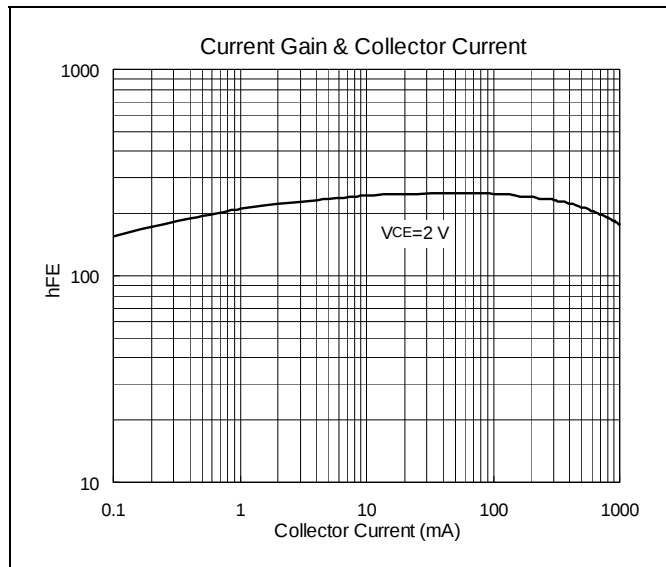
*Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

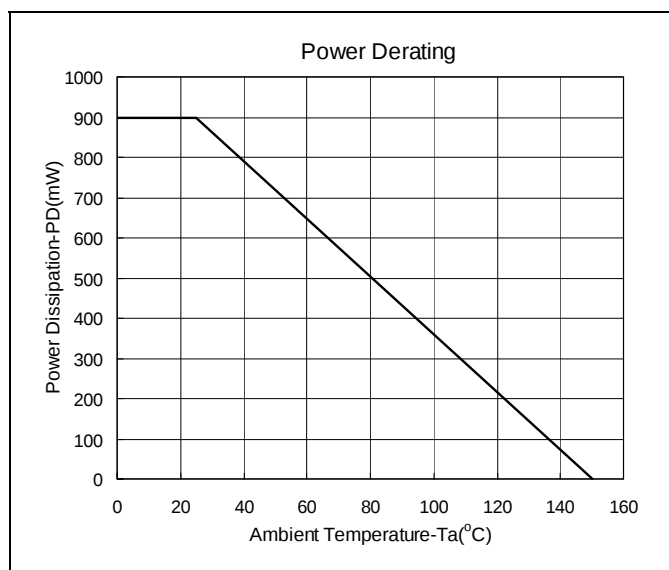
Classification Of h_{FE}

Rank	B	C
Range	85-170	120-240



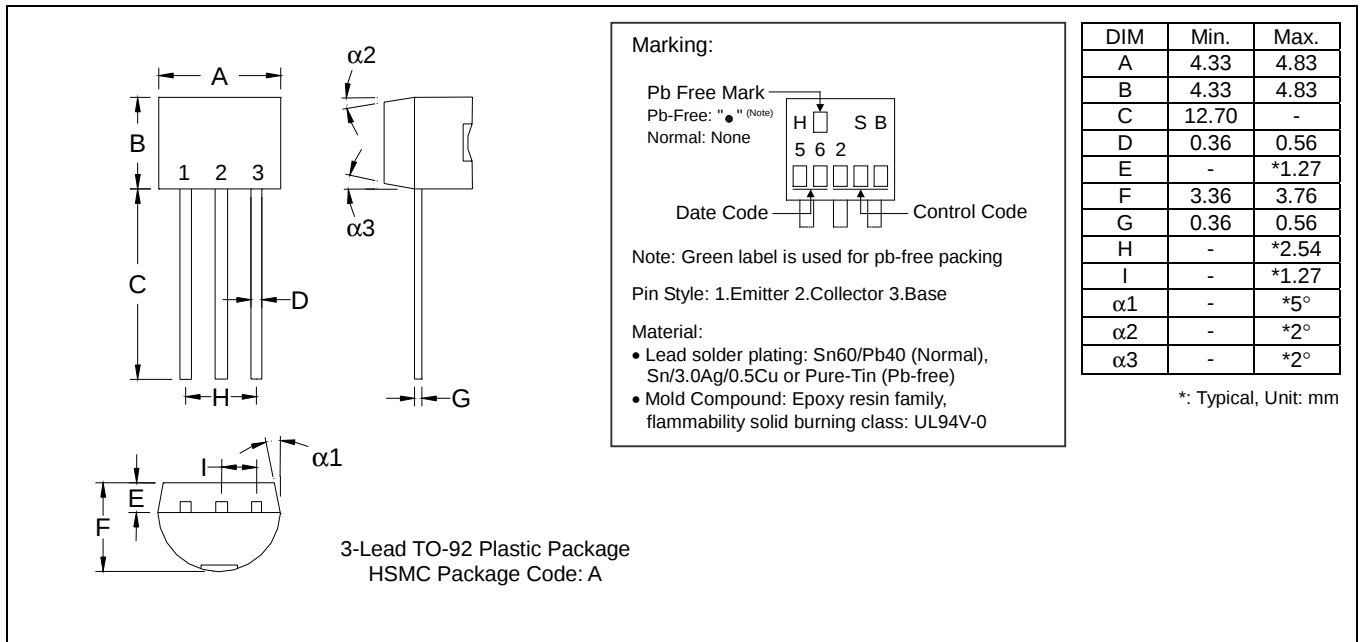
Characteristics Curve



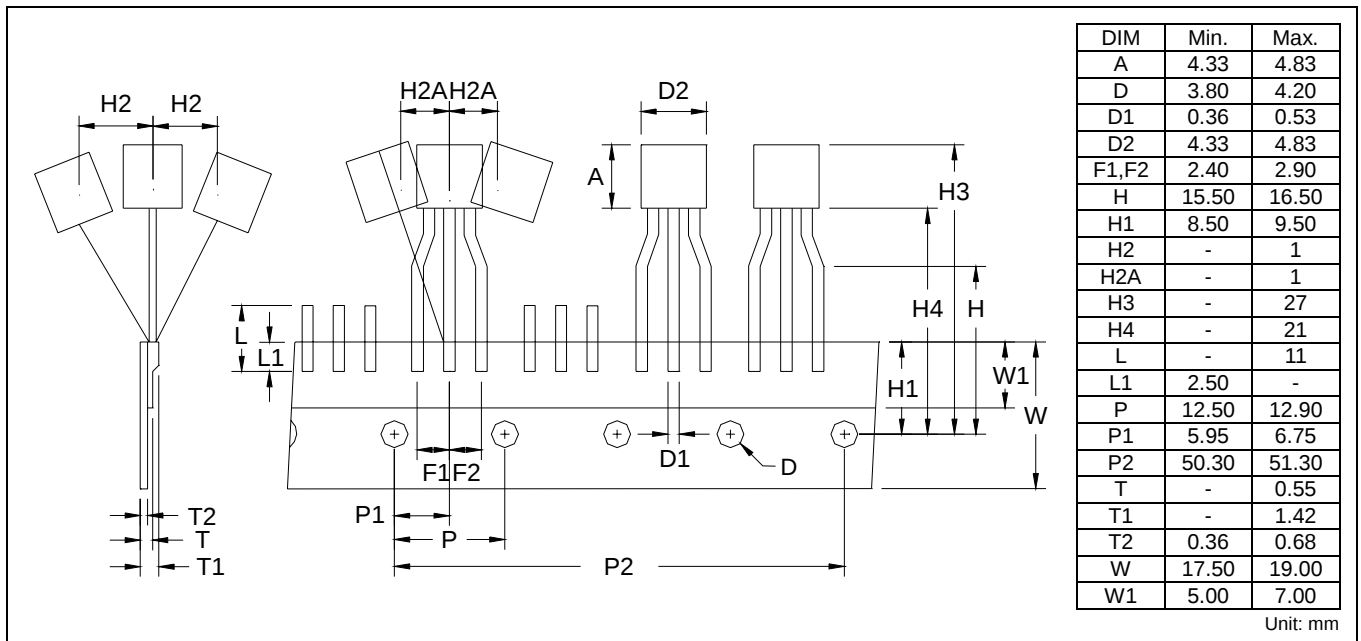




TO-92 Dimension



TO-92 Taping Dimension



Important Notice:

- All rights are reserved. Reproduction in whole or in part is prohibited without the prior written approval of HSMC.
- HSMC reserves the right to make changes to its products without notice.
- HSMC semiconductor products are not warranted to be suitable for use in Life-Support Applications, or systems.**
- HSMC assumes no liability for any consequence of customer product design, infringement of patents, or application assistance.

Head Office And Factory:

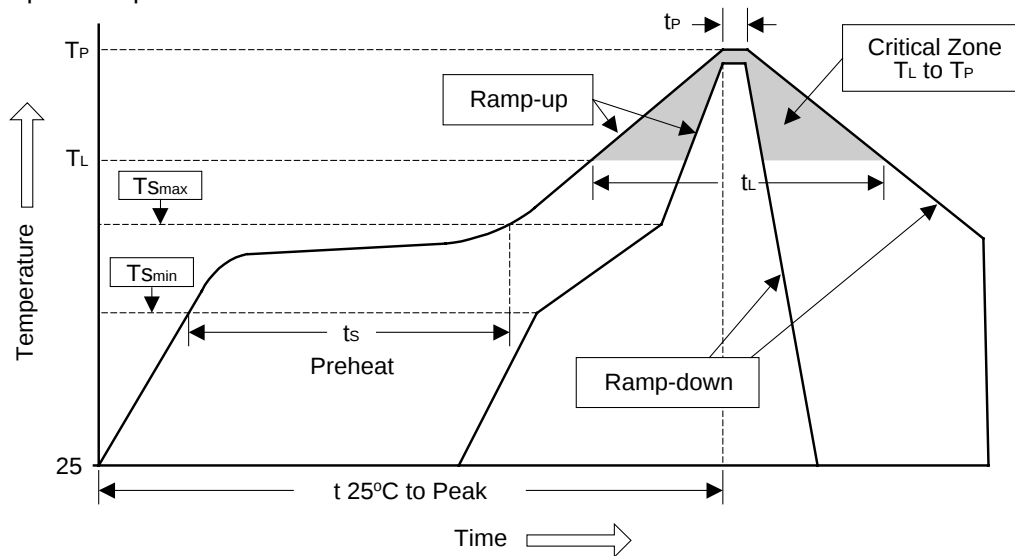
- Head Office** (Hi-Sincerity Microelectronics Corp.): 10F., No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
Tel: 886-3-5983621~5 Fax: 886-3-5982931



Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices

Figure 1: Temperature profile



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T_{smin})	100°C	150°C
- Temperature Max (T_{smax})	150°C	200°C
- Time (min to max) (t_s)	60~120 sec	60~180 sec
T_{smax} to T_L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T_L)	183°C	217°C
- Time (t_L)	60~150 sec	60~150 sec
Peak Temperature (T_P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec